

L Number	Hits	Search Text	l no	Trimo chama
- 19dimer	18		DB USPAT;	Time stamp 2002/07/23 16:02
	10	laser adj thermar adj annearys	US-PGPUB;	2002/07/23 10.02
			EPO; JPO;	1
			DERWENT;	
			IBM TDB	
-	3922	laser adj anneal\$3	USPAT;	2002/07/23 16:28
			US-PGPUB;	
1			EPO; JPO;	
]			DERWENT;	
1_	23	(laser adj anneal\$3) with ((source and	IBM_TDB USPAT;	2002/07/23 16:04
	23	drain) adj region)	US-PGPUB;	2002/01/23 10:04
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	(laser adj anneal\$3) with (continous adj	USPAT;	2002/07/23 16:40
		puls\$3)	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
-	l 0	(laser adj anneal\$3) with (mutli\$3 adj	USPAT;	2002/07/23 16:40
		puls\$3)	US-PGPUB;	-302, 5., 25 10.40
			EPO; JPO;	
]			DERWENT;	
	200	(1	IBM_TDB	0000/07/22 22
_	380	(laser adj anneal\$3) with puls\$3	USPAT; US-PGPUB;	2002/07/23 16:30
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	33	((laser adj anneal\$3) with puls\$3) with	USPAT;	2002/07/23 16:31
		continuous	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	0	 (laser adj anneal\$3) with (continuous adj	USPAT;	2002/07/23 17:04
		puls\$3)	US-PGPUB;	2002,01,23 11.04
			EPO; JPO;	
			DERWENT;	
	_	(1	IBM_TDB	0000/05/00 55
-	3	(laser adj anneal\$3) with (multi\$3 adj puls\$3)	USPAT; US-PGPUB;	2002/07/23 16:41
		 hara421	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	(laser adj anneal\$3) near (continuous adj	USPĀT;	2002/07/23 17:01
		puls\$3)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	7	(laser adj anneal\$3) and (continuous adj	IBM_TDB USPAT;	2002/07/23 17:07
	,	puls\$3)	US-PGPUB;	
		-	EPO; JPO;	
]			DERWENT;	
			IBM_TDB	
-	1	(laser adj anneal\$3) with (continuous near	USPAT;	2002/07/23 17:05
		puls\$3)	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	31584	ion adj implant\$3	USPAT;	2002/07/23 17:07
		· -	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	ا م	(ion adj implant\$3) and (laser adj	IBM_TDB USPAT;	2002/07/23 18:27
	١	anneal\$3 with (continuous or multi) adj	US-PGPUB;	2002/01/23 18:21
		pulse)	EPO; JPO;	
		\ -	DERWENT;	
			IBM_TDB	

- 0 (ion adj implant\$3) and (laser adj pulse) 0 0 (ion adj implant\$3) and (laser adj anneal\$3 mith ((continuous or multi) adj pulse) 1486 (continuous or multi) adj pulse) 0 0 0 0 0 0 0 0 0		,			
Pulse) EPO; JPO; DORWENT; IEM TOB USPAT; US-ECPUB; EPO; JPO; DERMENT; IEM TOB USPAT; USPAC; USPAT;	_	0	(==== === ====== (=== (==============	USPAT;	2002/07/23 17:10
1		į.	anneal\$3 with ((continuous or multi) adj	US-PGPUB;	
1			pulse))	EPO; JPO;	
1 (ion adj implant\$3) and (laser adj usp&RT usp&RT) 2002/07/23 17:13 2002/07/23 17		1		DERWENT;	
anneals3 and ((continuous or multi) adj pulse)) 1486 1486 activat\$3 with (ion adj implant\$3) - 29 (activat\$3 with (ion adj implant\$3)) with (laser adj anneal\$3) - 29 (activat\$3 with (ion adj implant\$3)) with (laser adj anneal\$3) - 21 (laser adj substrate) with mov\$3 - 21 (laser adj substrate) with mov\$3) with (activat\$3 with (ion adj implant\$3)) with (activat\$3 with (ion adj implant\$3)) with (activat\$3 with (ion adj implant\$3)) - 0 ((laser adj substrate) with mov\$3) with (activat\$3 with (ion adj implant\$3)) - 0 ((laser adj substrate) with mov\$3) and (activat\$3 with (ion adj implant\$3)) - 0 ((laser adj substrate) with mov\$3) with (activat\$3 with (ion adj implant\$3)) - 0 ((laser adj substrate) with mov\$3) with (activat\$3 with (ion adj implant\$3)) - 0 ((laser adj substrate) with mov\$3) with (activat\$3 with (ion adj implant\$3)) - 0 ((laser adj substrate) with mov\$3) with (activat\$3 with (ion adj implant\$3)) - 0 ((laser adj substrate) with mov\$3) with (activat\$3 with (ion adj implant\$3)) - 0 ((laser adj substrate) with mov\$3) with (activat\$3 with (ion adj implant\$3)) - 0 ((laser adj substrate) with mov\$3) with (activat\$3 with (ion adj implant\$3)) - 0 ((laser adj substrate) with mov\$3) with (activat\$3 with (ion adj implant\$4) with mov\$3) with (activat\$3 with (ion adj implant\$4) with mov\$3) with (activat\$3 with (ion adj implant\$4) with mov\$3) and (activat\$3 with (ion adj implant\$4) with mov\$3 and (activat\$3 with (ion adj implant\$4) with mov\$3) and (activat\$3 with (ion adj implant\$4) and activat\$3 with (activat\$3 with (ion adj implant\$3)) (activat\$3 with (ion adj implant\$3)) (activat\$3 with (ion adj implant\$3		İ	•	IBM TDB	
Depty Dept	-	1		USPAT;	2002/07/23 17:13
DEMENT: IDM TOB USPAT: US-PGPUB; EPO; JPO; DERWENT: IDM TOB USPAT: US-PGPUB; EPO; JPO; JPO; DERWENT: IDM TOB USPAT: US-PGPUB; EPO; JPO; JPO; JPO; JPO; J				US-PGPUB;	
DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGP			pulse))	EPO; JPO;	
1486 activat\$3 with (ion adj implant\$3)				DERWENT;	}
US-PGPUB; EDG JPG DERMENT; IBM TOB USPAT; US-PGPUB; EPG JPG DERMENT; IBM				IBM TDB	
Company	-	1486	activat\$3 with (ion adj implant\$3)	USPAT;	2002/07/23 18:39
Company	ļ			US-PGPUB;	
Cactivat\$3 with (ion adj implant\$3) with (laser adj anneal\$3) with (laser adj anneal\$3) with (laser adj substrate) with mov\$3 USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; US-PGPUB; EPG					
- 29				DERWENT;	
Claser adj anneal\$3 US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; D	1			IBM TDB	
- 21 (laser adj substrate) with mov\$3	-	29		USPAT;	2002/07/23 18:34
- 21 (laser adj substrate) with mov\$3 DERMENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERMENT; US-PGPUB; EPO;			(laser adj anneal\$3)	US-PGPUB;	
Company				EPO; JPO;	
-		J		DERWENT;	
-		İ		IBM TDB	
US-PGPUB; EPO; JPO; DERWENT; IBM TDB US-PAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB;	-	21	(laser adj substrate) with mov\$3	USPAT;	2002/07/23 18:44
- 0 ((laser adj substrate) with mov\$3) with (activat\$3 with (ion adj implant\$3)) - 0 ((laser adj substrate) with mov\$3) and (activat\$3 with (ion adj implant\$3)) - 0 ((laser adj substrate) with mov\$3) and (activat\$3 with (ion adj implant\$3)) - 0 ((laser adj substrate) with mov\$3) with activat\$3 with (ion adj implant\$3)) - 10 ((laser adj substrate) with mov\$3) with activat\$3 - 147 (laser near substrate) with mov\$3) with activat\$3 - 147 (laser near substrate) with mov\$3 - 11 ((laser near substrate) with mov\$3) and ion adj implant\$4 - 2014 (laser with substrate) with mov\$3 - 2014 (laser with substrate) with mov\$3 and ion adj implant\$4 - 2014 (laser with substrate) with mov\$3 and ion adj implant\$4 - 2014 (laser with substrate) with mov\$3 and ion adj implant\$4 - 2015 ((laser with substrate) with mov\$3) and ion adj implant\$4 - 2016 ((laser with substrate) with mov\$3) and ion adj implant\$4 - 2017 (vlaser with substrate) with mov\$3 and ion adj implant\$4 - 2018 (vlaser with substrate) with mov\$3 and ion adj implant\$4 - 2019 (vlaser with substrate) with mov\$3 and ion adj implant\$4 - 2019 (vlaser with substrate) with mov\$3 and ion adj implant\$4 - 2019 (vlaser with substrate) with mov\$3 and ion adj implant\$4 - 2019 (vlaser with substrate) with mov\$3 and ion adj implant\$4 - 2019 (vlaser with substrate) with mov\$3 and ion adj implant\$4 - 2019 (vlaser with substrate) with mov\$3 and ion adj implant\$4 - 2019 (vlaser with substrate) with mov\$3 and ion adj implant\$4 - 2019 (vlaser with substrate) with mov\$3 and ion adj implant\$4 - 2019 (vlaser with substrate) with mov\$3 and ion adj implant\$4 - 2019 (vlaser with substrate) with mov\$3 and ion adj implant\$4 - 2019 (vlaser with substrate) with mov\$3 and ion adj implant\$4 - 2019 (vlaser with substrate) with mov\$3 - 2002/07/23 18:51 - 2002/07/23 18:51 - 2002/07/23 18:51 - 2002/07/23 18:51 - 2002/07/23 18:51				US-PGPUB;	
Comparison				1	
TBM TDB	İ				
Company Comp					
Cactivat\$3 with (ion adj implant\$3) US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IPO	-	j 0	((laser adj substrate) with mov\$3) with		2002/07/23 18:39
Company Comp			(activat\$3 with (ion adj implant\$3))	1	
- 0 ((laser adj substrate) with mov\$3) and (activat\$3 with (ion adj implant\$3)) - 0 ((laser adj substrate) with mov\$3) with activat\$3 - 0 ((laser adj substrate) with mov\$3) with activat\$3 - 147 (laser near substrate) with mov\$3 - 147 (laser near substrate) with mov\$3 - 11 ((laser near substrate) with mov\$3) and ion adj implant\$4 - 2014 (laser with substrate) with mov\$3 - 2014 (laser with substrate) with mov\$3 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 - 30 ((((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3			- ' -	1	
Company					
Company					
(activat\$3 with (ion adj implant\$3) US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT;	-	0	((laser adj substrate) with mov\$3) and		2002/07/23 18:39
- 0 ((laser adj substrate) with mov\$3) with activat\$3 - 147 (laser near substrate) with mov\$3 - 11 ((laser near substrate) with mov\$3 - 11 ((laser near substrate) with mov\$3) and ion adj implant\$4 - 2014 (laser with substrate) with mov\$3 - 68 ((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3			(activat\$3 with (ion adj implant\$3))		
DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT;				•	
Comparison of the control of the c					
- 0 ((laser adj substrate) with mov\$3) with activat\$3 - 147 (laser near substrate) with mov\$3 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGP	ĺ			,	
activat\$3	-	0	((laser adj substrate) with mov\$3) with	ı -	2002/07/23 18:51
Tem Tob				1	10.01
- 147 (laser near substrate) with mov\$3 - 11 ((laser near substrate) with mov\$3) and ion adj implant\$4 - 2014 (laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4			_	1	
- 147 (laser near substrate) with mov\$3 - 11 ((laser near substrate) with mov\$3) and ion adj implant\$4 - 2014 (laser with substrate) with mov\$3 - 68 ((laser with substrate) with mov\$3) and ion adj implant\$4 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 - 30 (((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3			·		
147 (laser near substrate) with mov\$3 USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO;					
US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DE	-	147	(laser near substrate) with mov\$3		2002/07/23 18:51
- 11 ((laser near substrate) with mov\$3) and ion adj implant\$4					10101, 07, 20 10, 01
- 11 ((laser near substrate) with mov\$3) and ion adj implant\$4]			EPO; JPO;	
- 11 ((laser near substrate) with mov\$3) and ion adj implant\$4 USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; ISM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; ISM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT;					
11 ((laser near substrate) with mov\$3) and ion adj implant\$4					
ion adj implant\$4 2014 (laser with substrate) with mov\$3 ((laser with substrate) with mov\$3 uspar; uspar; lbm tdb uspar; lbm	-	11			2002/07/23 18:45
2014 (laser with substrate) with mov\$3 (laser with substrate) with mov\$3 (laser with substrate) with mov\$3 and ion adj implant\$4 ((laser with substrate) with mov\$3) and ion adj implant\$4 ((laser with substrate) with mov\$3) and ion adj implant\$4 ((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 ((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;			ion adj implant\$4		
- 2014 (laser with substrate) with mov\$3 (laser with substrate) with mov\$3 (laser with substrate) with mov\$3 and ion adj implant\$4 ((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;					
- 2014 (laser with substrate) with mov\$3 ((laser with substrate) with mov\$3 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;				DERWENT;	l
- 68 ((laser with substrate) with mov\$3) and ion adj implant\$4 ((laser with substrate) with mov\$3) and ion adj implant\$4 ((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 ((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 (2002/07/23 18:52			•		
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	-	2014	(laser with substrate) with mov\$3	USPAT;	2002/07/23 18:51
- 68 ((laser with substrate) with mov\$3) and ion adj implant\$4 ((laser with substrate) with mov\$3) and ion adj implant\$4 ((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 ((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 (2002/07/23 18:52 US-PGPUB; EPO; JPO; DERWENT; EPO; JPO; DERWENT;				US-PGPUB;	- 1
- 68 ((laser with substrate) with mov\$3) and ion adj implant\$4 ((laser with substrate) with mov\$3) and ion adj implant\$4 ((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 ((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 (see EPO; JPO; DERWENT; EPO; JPO; DERWENT;					
- 30 (((laser with substrate) with mov\$3) and ion adj implant\$4 (((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 (((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 (2002/07/23 18:51 US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;				DERWENT;	
ion adj implant\$4 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; DERWENT;				IBM_TDB	
ion adj implant\$4 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; Ion adj implant\$4) and activat\$3 US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	-	68		USPĀT;	2002/07/23 18:51
- 30 (((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;			ion adj implant\$4	US-PGPUB;	
- 30 (((laser with substrate) with mov\$3) and ion adj implant\$4) and activat\$3 IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;				EPO; JPO;	
- 30 (((laser with substrate) with mov\$3) and USPAT; 2002/07/23 18:52 ion adj implant\$4) and activat\$3 US-PGPUB; EPO; JPO; DERWENT;				DERWENT;	
- 30 (((laser with substrate) with mov\$3) and USPAT; 2002/07/23 18:52 ion adj implant\$4) and activat\$3 US-PGPUB; EPO; JPO; DERWENT;				IBM_TDB	
EPO; JPO; DERWENT;	-	30	(((laser with substrate) with mov\$3) and		2002/07/23 18:52
DERWENT;			ion adj implant\$4) and activat\$3		
DERWENT;				EPO; JPO;	
IBM TDB					İ
				IBM_TDB	